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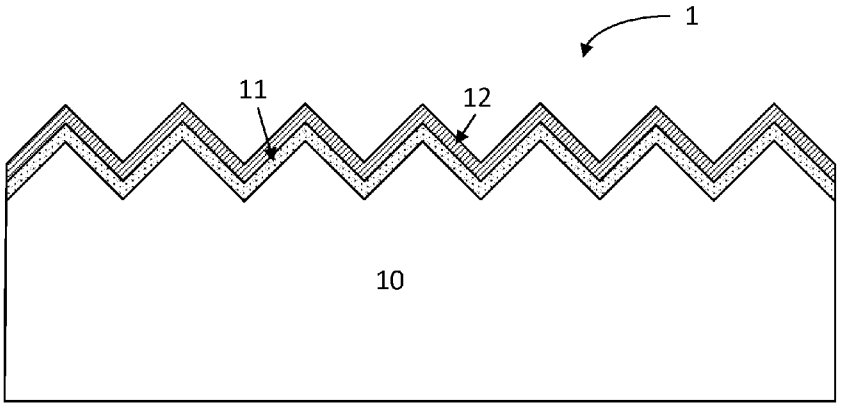
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(54) Title: METHOD FOR FORMING METAL SILICIDE LAYERS



1(a)

(57) Abstract: The present invention is related to a method for forming a metal silicide layer on a textured silicon substrate surface, the method comprising: providing a metal layer on a textured silicon substrate; and performing a pulsed laser annealing step providing at least one UV laser pulse with a laser fluence in the range between 0.1 J/cm2 and 1.5 J/cm2 and with a laser pulse duration in the range between 1 ns and 10 ms, thereby converting at least part of the metal layer into a metal silicide layer. In addition, the present invention is related to the use of such method in a process for fabricating a photovoltaic cell, wherein the dielectric layer is a surface passivation layer, or wherein the dielectric layer is an antireflection coating.

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